

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

# 2SA965

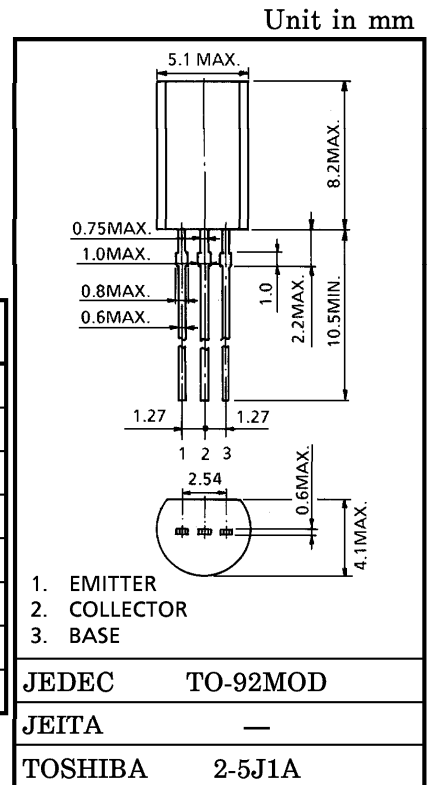
POWER AMPLIFIER APPLICATIONS

DRIVER STAGE AMPLIFIER APPLICATIONS

- Complementary to 2SC2235.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V <sub>CB0</sub>	-120	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-120	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current	I <sub>C</sub>	-800	mA
Emitter Current	I <sub>E</sub>	800	mA
Collector Power Dissipation	P <sub>C</sub>	900	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55~150	°C

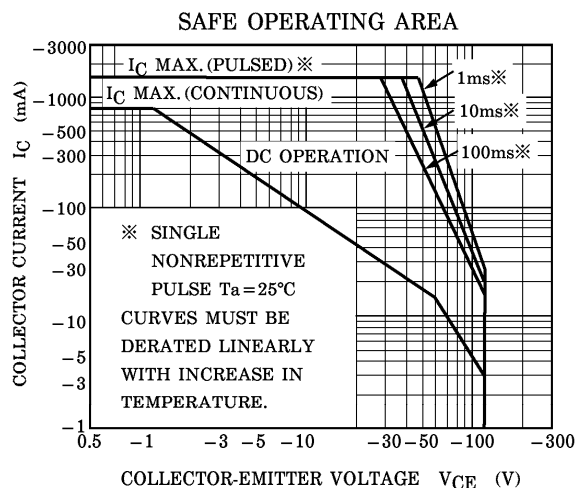
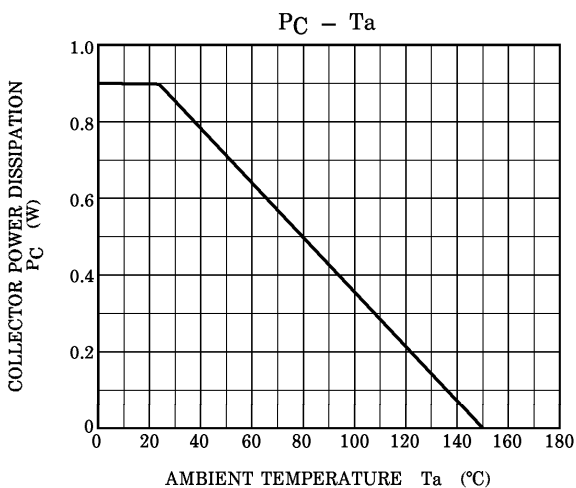
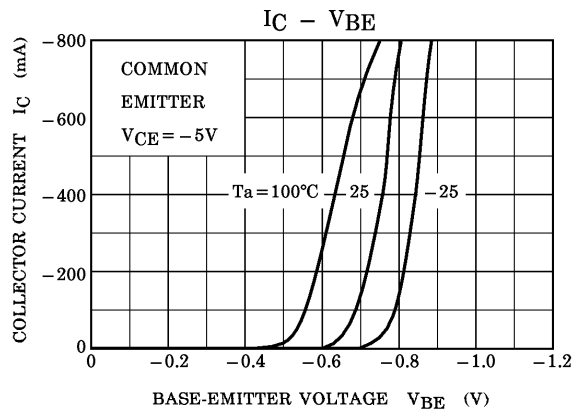
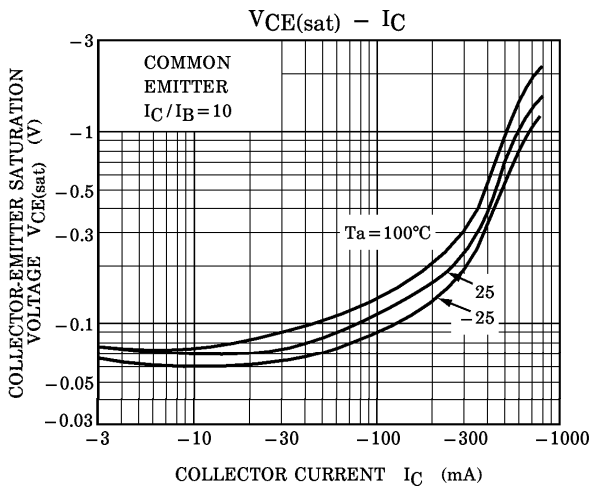
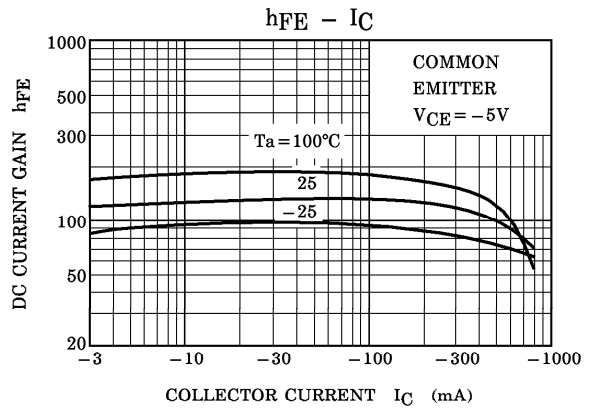
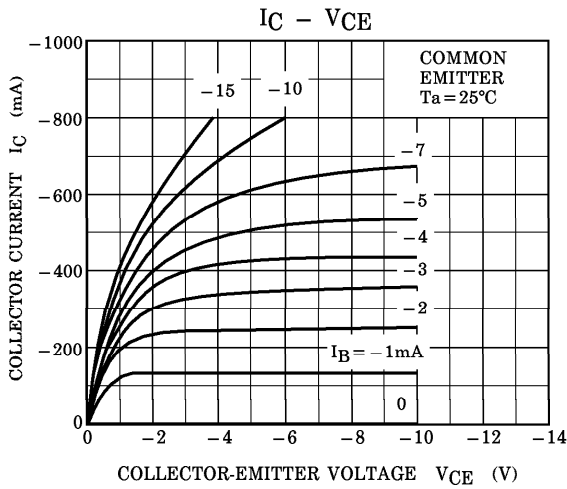


ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Weight : 0.36g (Typ.)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I <sub>CB0</sub>	V <sub>CB</sub> = -120V, I <sub>E</sub> = 0	—	—	-100	nA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> = 0	—	—	-100	nA
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -10mA, I <sub>B</sub> = 0	-120	—	—	V
Emitter -Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -1mA, I <sub>C</sub> = 0	-5	—	—	V
DC Current Gain	h <sub>FE</sub> (Note)	V <sub>CE</sub> = -5V, I <sub>C</sub> = -100mA	80	—	240	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA	—	—	-1.0	V
Base-Emitter Voltage	V <sub>BE</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -500mA	—	—	-1.0	V
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -100mA	—	120	—	MHz
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10V, I <sub>E</sub> = 0, f = 1MHz	—	—	40	pF

(Note) : h<sub>FE</sub> Classification O : 80~160, Y : 120~240



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